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| APPLICATION NO. | FILING DATE | FIRST NAMED INVENTOR | ATTORNEY DOCKET NO. | CONFIRMATION NO. |
|---------------------------------------|---------------|----------------------|-------------------------|------------------|
| 09/670,877 | 09/27/2000 | KAZUO ICHIKAWA | . 107469 | 7376 |
| 75 | 90 02/26/2002 | | | |
| OLIFF & BERRIDGE PLC | | | EXAMINER | |
| P O BOX 19928 ALEXANDRIA, VA 22320 | | ZERVIGON, RUDY | | |
| | | | ART UNIT | PAPER NUMBER |
| | | | 1763 | 4 |
| | | | DATE MAILED: 02/26/2002 | |

Please find below and/or attached an Office communication concerning this application or proceeding.

| • | | Application No. | <u> </u> | | | |
|---|--|---|---|--|--|--|
| | • | Application No. | Applicant(s) | | | |
| Office Action Summary | | 09/670,877 | ICHIKAWA ET AL. | | | |
| | omeon dummary | Examiner | Art Unit | | | |
| <u> </u> | The MAIL ING DATE of this communication ann | Rudy Zervigon | 1763 | | | |
| Periodic | | | | | | |
| - Exte after - If the - If NC - Failu - Any | ORTENED STATUTORY PERIOD FOR REPLY MAILING DATE OF THIS COMMUNICATION. nsions of time may be available under the provisions of 37 CFR 1.13 SIX (6) MONTHS from the mailing date of this communication. It period for reply specified above is less than thirty (30) days, a reply operiod for reply is specified above, the maximum statutory period we re to reply within the set or extended period for reply will, by statute, eply received by the Office later than three months after the mailing and patent term adjustment. See 37 CFR 1.704(b). | 36(a). In no event, however, may a reply be to within the statutory minimum of thirty (30) day ill apply and will expire SIX (6) MONTHS from Cause the application to become ARANDON. | imely filed ays will be considered timely. In the mailing date of this communication. | | | |
| 1)🖂 | Responsive to communication(s) filed on 27 S | September 2000 . | | | | |
| 2a) <u></u> | | s action is non-final. | | | | |
| 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213. Disposition of Claims | | | | | | |
| 4)🖂 | Claim(s) <u>1-4</u> is/are pending in the application. | | | | | |
| 4a) Of the above claim(s) is/are withdrawn from consideration. | | | | | | |
| 5) | Claim(s) is/are allowed. | | | | | |
| 6)⊠ | Claim(s) <u>1-4</u> is/are rejected. | | | | | |
| 7) | Claim(s) is/are objected to. | | | | | |
| 8)□ | Claim(s) are subject to restriction and/or | election requirement. | | | | |
| | on Papers | | | | | |
| 9)[] 7 | The specification is objected to by the Examiner | | | | | |
| 10)□ 1 | he drawing(s) filed on is/are: a)☐ accept | ted or b) \square objected to by the Exa | miner. | | | |
| | Applicant may not request that any objection to the | drawing(s) be held in abeyance. S | See 37 CFR 1.85(a). | | | |
| 11) 🔲 T | he proposed drawing correction filed on | is: a) ☐ approved b) ☐ disappro | oved by the Examiner. | | | |
| | If approved, corrected drawings are required in repl | | | | | |
| 12) <u> </u> | he oath or declaration is objected to by the Exa | miner. | | | | |
| Priority u | nder 35 U.S.C. §§ 119 and 120 | | | | | |
| 13)🛛 | Acknowledgment is made of a claim for foreign | priority under 35 U.S.C. § 119(a | a)-(d) or (f). | | | |
| a)⊠ All b)□ Some * c)□ None of: | | | | | | |
| | 1.⊠ Certified copies of the priority documents have been received. | | | | | |
| ; | 2. Certified copies of the priority documents have been received in Application No | | | | | |
| | 3. Copies of the certified copies of the priorit application from the International Bure se the attached detailed Office action for a list o | ty documents have been receive eau (PCT Rule 17.2(a)). | ed in this National Stage | | | |
| | cknowledgment is made of a claim for domestic | • | | | | |
| a) | ☐ The translation of the foreign language prov | isional application has been rec | eived. | | | |
| 15)[] A | cknowledgment is made of a claim for domestic | | | | | |
| Attachment(| | | | | | |
| 2) Notice | of References Cited (PTO-892) of Draftsperson's Patent Drawing Review (PTO-948) ation Disclosure Statement(s) (PTO-1449) Paper No(s) <u>2</u> . | | (PTO-413) Paper No(s) Patent Application (PTO-152) | | | |
| S. Patent and Trac PTO-326 (Rev. | | on Summary | Part of Paper No. 4 | | | |

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DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

2. Claims 1-4 are rejected under 35 U.S.C. 102(b) as being anticipated by Hara et al (U. S. Pat. 5,648,276). Hara et al teaches a CVD system (C₁, C₂; Figure 2; column 7, lines 7-8) provided with a plasma generator (Fig.3, "UE", column 7, lines 15-20) having a plasma generation chamber (Fig. 3 containing "PL"; column 7, lines 15-20) separated from a film deposition chamber (Fig. 3 "QW" and "SW"; column 7, lines 10-15) in which a substrate (1) is arranged. A material gas (Fig.3, "Gas (SiH₄, etc)") is directly supplied into the film deposition chamber, radicals in the plasma are introduced into the film deposition chamber from the plasma generator through introduction holes ("ME", Fig.3), and a thin film ("a-Si:H", column 7, lines 5-10) is deposited on the substrate. A gas feeder ("Gas (Ar, ...)"; Fig.3) is provided to the plasma generator.

Hara et al further teaches a cleaning method whereby a silicon-based film is deposited on a substrate ("a-Si:H", column 7, lines 5-10, lines 65-67), then converting the silicon-based film to a crystalline silicon-based film by laser annealing (column 8, lines 5-11), then depositing a gate insulating film ("SiO₂"; column 8, lines 20-25) on the crystalline film by a CVD system comprised of a separate film deposition chamber and plasma generation chamber as described

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above. Plasma "cleaning" is discussed as a step prior to forming the gate insulating film (column

13, lines 9-20). See cal. 14, lines 10-25 and cal. 17, lines 1-10.

2/25/02

Conclusion

3. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. U.S.Pat. 6,182,603; 5,834,068; 5,449,410; 6,029,602.

4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Examiner Rudy Zervigon whose telephone number is (703) 305-1351. The examiner can normally be reached on a Monday through Thursday schedule from 8am through 7pm. The official after final fax phone number for the 1763 art unit is (703) 872-9311. The official before final fax phone number for the 1763 art unit is (703) 872-9310. Any Inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Chemical and Materials Engineering art unit receptionist at (703) 308-0661. If the examiner can not be reached please contact the examiner's supervisor, Gregory L. Mills, at (703) 308-1633.

GREGORY MILLS SUPERVISORY PATENT EXAMINER TECHNOLOGY CENTER 1700